

### **INCHANGE SEMICONDUCTOR**

# isc N-Channel MOSFET Transistor

## SPW11N60CFD

# ISPW11N60CFD

### • FEATURES

- Static drain-source on-resistance:  $R_{DS}(on) \leqslant 440 m_{\Omega}$
- · Enhancement mode:
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### DESCRITION

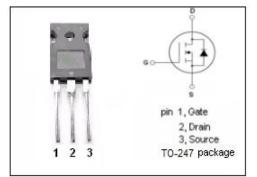
High peak current capability

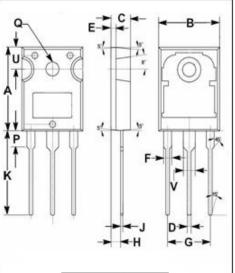
### • ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

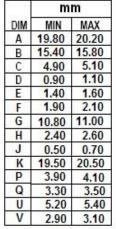
SYMBOL	PARAMETER	VALUE	UNIT
V <sub>DSS</sub>	Drain-Source Voltage	600	V
V <sub>GS</sub>	Gate-Source Voltage	±20	V
ID	Drain Current-Continuous	11	А
I <sub>DM</sub>	Drain Current-Single Pulsed	28	А
PD	Total Dissipation @Tc=25°C	125	W
Tj	Max. Operating Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-55~150	°C

#### • THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	МАХ	UNIT
Rth(j-c)	Channel-to-case thermal resistance	1	°C/W
Rth(j-a)	Channel-to-ambient thermal resistance	62	°C/W







isc website: www.iscsemi.cn



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### **ELECTRICAL CHARACTERISTICS**

#### $T_{\text{C}}\text{=}25^\circ\!\!\mathbb{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V; I <sub>D</sub> =0.25mA	600			V
$V_{GS(th)}$	Gate Threshold Voltage	VDS=VGS; ID=0.5mA	3		5	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> =10V; I <sub>D</sub> =7 A			440	mΩ
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> = 20V; V <sub>DS</sub> = 0V			0.1	μ <b>Α</b>
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =600V; V <sub>GS</sub> = 0V			1.1	μA
V <sub>SD</sub>	Diode forward voltage	I <sub>F</sub> =IS, V <sub>GS</sub> = 0V			1.2	V

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